

isc Silicon NPN RF Transistor

2SC2757

DESCRIPTION

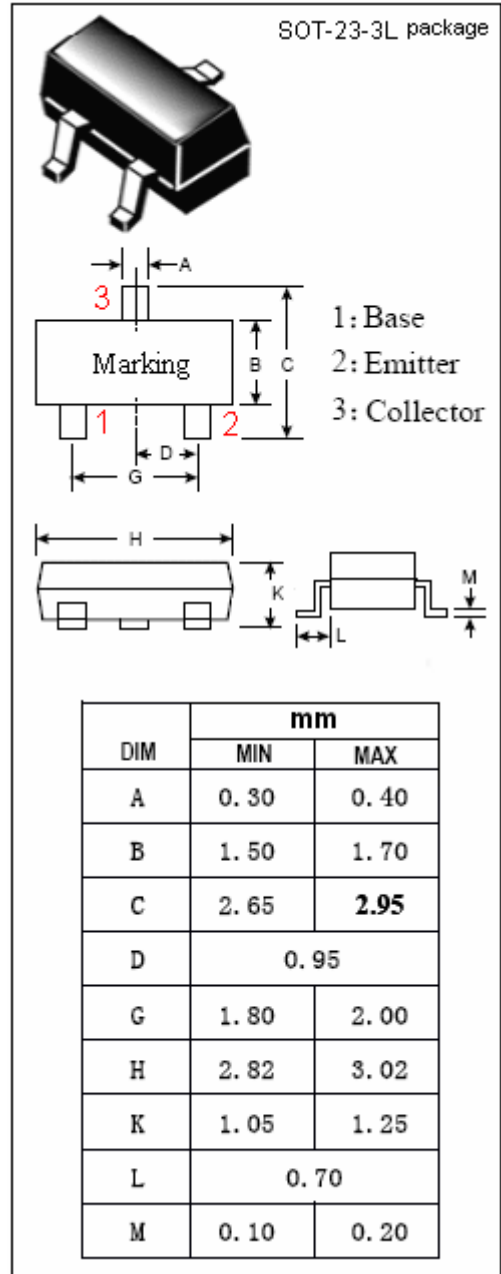
- Low Noise
- High Current-Gain Bandwidth Product

APPLICATIONS

- Designed for use in VHF RF amplifier, local oscillator, mixer.

ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	30	V
V <sub>CEO</sub>	Collector-Emitter Voltage	15	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current-Continuous	50	mA
P <sub>C</sub>	Collector Power Dissipation @T <sub>C</sub> =25°C	0.15	W
T <sub>J</sub>	Junction Temperature	125	°C
T <sub>stg</sub>	Storage Temperature Range	-55~125	°C



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## ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=10\text{mA}$ ; $I_B=1\text{mA}$			0.5	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB}=12\text{V}$ ; $I_E=0$			0.1	$\mu\text{A}$
$h_{FE}$	DC Current Gain	$I_C=5\text{mA}$ ; $V_{CE}=10\text{V}$	60		240	
$f_T$	Current-Gain—Bandwidth Product	$I_C=5\text{mA}$ ; $V_{CE}=10\text{V}$	800	1100		MHz
$C_{OB}$	Output Capacitance	$I_E=0$ ; $V_{CB}=10\text{V}$ ; $f=1.0\text{MHz}$			1.5	pF
$\tau_{bb'} \cdot CC$	Base Time Constant	$I_C=5\text{mA}$ ; $V_{CB}=10\text{V}$ ; $f=31.9\text{MHz}$		10	15	ps

◆  $h_{FE}$  Classifications

Marking	T32	T33	T34
$h_{FE}$	60-120	90-180	120-240